

REMARKS

Reconsideration of this application is requested. Claims 18-30 are active in the application subsequent to entry of this amendment.

Item 14 of the Action indicates claims 9-11 to be directed to allowable subject matter. With this comment in mind the feature of previous claim 9 has now been included in all of the independent claims presented above. It is respectfully submitted that the claims are patentable and also free from informalities and objections of the type mentioned in items 2-4 of the Official Action.

With regard to the examiner's questions about Fig. 2 of the drawings and the associated description in the examples, layer 23 is a superlattice layer – *see* the description at page 29, line 14, Example 5. The description of Example 8 has been adjusted to agree with the drawings.

Please also consider the concurrently filed Information Disclosure Statement.

Further consideration and favorable action are solicited.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION

The paragraph beginning at page 38, line 24 through page 39, line 2

The LD device is fabricated in the same manner as in Example 5 [as shown in Fig. 2 (showing the device cut in the parallel direction to the resonating plane of the laser, an example of LD device according to the first embodiment of the present invention], except for the n-type contact layer.:

The paragraph beginning at page 39, lines 9-12:

Subsequently, at 1020°C, using silane gas as an impurity gas, a second nitride semiconductor layer [23] (the n-type contact layer) made of Si doped n-type GaN is grown. The resistivity of the resulting LD device was also  $5 \times 10^{-3} \Omega \cdot \text{cm}$ .